

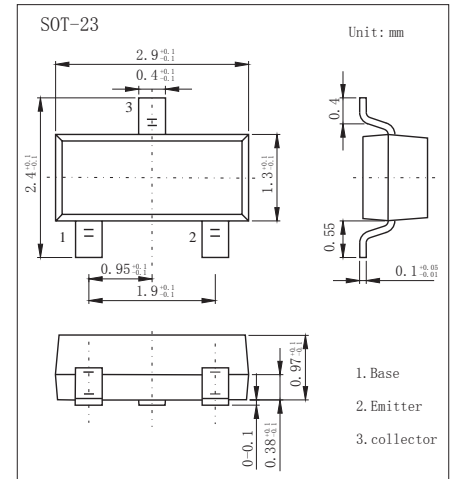
SOT-23 Plastic-Encapsulate Transistors

FEATURES

- TRANSISTOR (PNP)
- Complement to KSC2859

MECHANICAL DATA

- Case style: SOT-23 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	-35	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.5	A
P_C	Collector Power Dissipation	150	mW
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55-150	°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -35V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -100mA$	70		240	
	$h_{FE(2)}$	$V_{CE} = -6V, I_C = -400mA$	25			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$			-0.25	V
Base-emitter voltage	V_{BE}	$V_{CE} = -1V, I_C = -100mA$			-1.0	V
Transition frequency	f_T	$V_{CE} = -6V, I_C = -20mA$		200		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -6V, I_E = 0, f = 1MHz$		13		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	70-140	120-240
Marking	F1O	F1Y